

**GR881 (8K x 8)  
NON-VOLATILE RAM**

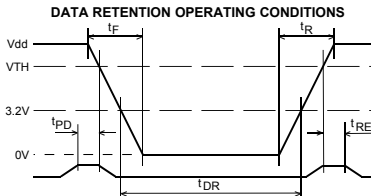


ABSOLUTE MAXIMUM RATINGS			
Symbol	Min	Max	Units
Vdd	-0.3	7.0	Volts
V <sub>IO</sub>	-0.3	Vdd +0.3	Volts
Temp	-20	+70	deg. C

OPERATING CONDITIONS				
Symbol	Min	Typ	Max	Unit
Vdd	4.75	5.0	5.5	Volts
Vin (1)	2.2		Vdd+0.3	Volts
Vin (0)	-0.3		0.8	Volts
Iin (any other pin)	-1.0		+1.0	µA
Vout (1)(I <sub>out</sub> = -1mA)	2.4			Volts
Vout (0)(I <sub>out</sub> = +2mA)			0.4	Volts
Idd (Active)		30		mA
Idd (Deselected)		1.0		mA
Tcycle		100		nS
Cin (any pin)		10		pF

OPERATING MODE					
CE	OE	WR	MODE	OUTPUT	Idd
H	X	X	Unsel.	Hi-Z	Standby
L	H	H	Unsel.	Hi-Z	Active
L	L	H	Read	Dout	Active
L	X	L	Write	Din	Active

PIN CONNECTIONS			PIN DESIGNATIONS		
NC	1	28	Vdd		
A12	2	27	WR	Pin	Function
A7	3	26	CE <sub>2</sub>	A0-A12	Address I/P's
A6	4	25	A8	D0-D7	Data in/out
A5	5	24	A9	OE	Output Enable
A4	6	23	A11	CE <sub>1</sub>	Chip Enable
A3	7	22	A10	WR	Write Enable
A2	8	21	A10	Vdd	+5Volt Power
A1	9	20	CE <sub>1</sub>		
A0	10	19	D7	GND	Ground
D0	11	18	D6		
D1	12	17	D5		
D2	13	16	D4		
GND	14	15	D3		



Symbol	Parameter	Min	Typ	Max	Units
Vdd	Operating supply voltage	4.75	5.0	5.50	Volts
VTH	Data retention voltage		4.5		Volts
t <sub>F</sub>	Vdd slew to 0V	15			µS
t <sub>R</sub>	Vdd slew 0V to 5.0V	15			µS
t <sub>REC</sub>	CE to O/P valid from power up		15		µS
t <sub>DR</sub>	Data retention time		10		Years
t <sub>PD</sub>	CE at Vin(1) before power down	0			µS

**DESCRIPTION**  
The GR881 is a 8192 word by 8 bits (8K x 8) non-volatile CMOS Static Ram, fabricated from advanced silicon gate CMOS technology and a high reliability lithium power cell.

The pin-out of the GR881 conforms to the JEDEC standards and is fully compatible with normal static RAM. The power down circuit is fully automatic and is referenced at 4.5 volts. At this point the GR881 is write protected by an internal inhibit function for Data Protection and the memory contents are retained by the lithium power source.

Power down is very fast, this being essential for data integrity, taking a maximum of 15 µS (15 microseconds) to power down from 5 volts to 0 volts. This is much faster than system power failure conditions. Therefore there are no special conditions required when installing the GR881.

The GR881 can, without external power, retain data almost indefinitely. The limiting factor will be the shelf life of the lithium cell, which is typically ten years. It is possible that this figure may be extended in view of the extremely light duty imposed upon the cell.

**APPLICATION**

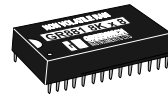
When powered down, the GR881 is transportable and data can be moved from system to system, this makes it ideal for program development, data collection in data loggers, program changes in process control, automation and robotics and user definable lookup tables, etc.

**DISPOSAL INSTRUCTIONS**

Do not dispose of non-volatile memory devices by incineration or crushing. Devices may be returned carriage paid to Greenwich Instruments Ltd., for disposal.

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Swanley, Kent. BR8 8AH  
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01322 668 724  
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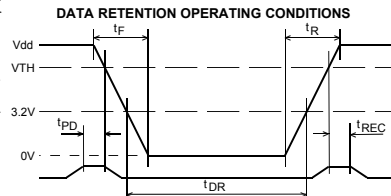


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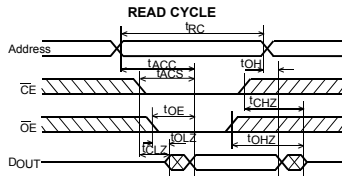
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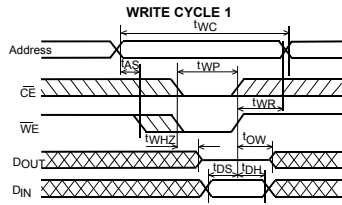
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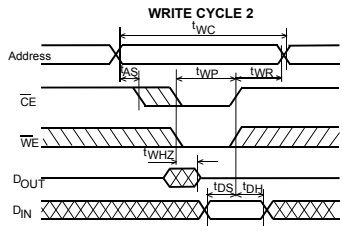


**TIMING (nS-nano seconds)**

Read Cycle		100nS	
Symbol	Parameter	Min	Max
tRC	Read cycle time	100	
tACC	Access time		100
tACS	CE to output valid		100
tOE	OE to output valid		40
tCLZ	CE to output active	10	
tOLZ	OE to output active	5	
tOH	Output hold time		10
tCHZ	CE to output disable		30
tOHZ	OE to output disable		20



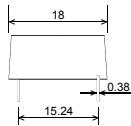
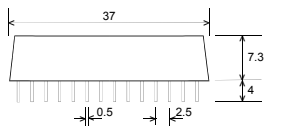
Write Cycle		100nS	
Symbol	Parameter	Min	Max
tWC	Write cycle time	100	
tWP	Write pulse width	60	
tAS	Address setup time	0	
tWR	Write recovery time	0	
tWHZ	WR to output disable		30
tOW	Output active from WR	10	
tDS	Data setup time	40	
tDH	Data HOLD TIME	0	



- Notes
1. WE must be high during address transitions.
  2. A Write occurs during the overlap of active CE and a low WE.
  3. CE = CE1 and CE2
  4. WE is high for a read cycle.

REPLACES ..... 6264., 5565., etc.

**DIMENSIONS (mm)**

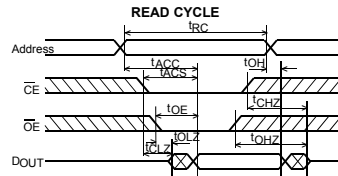


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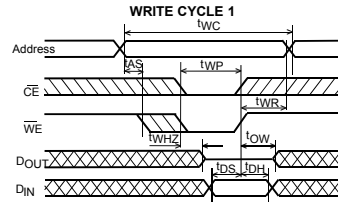
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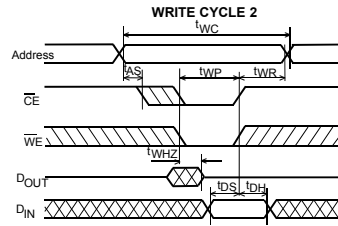


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tOH	Output hold time		10
tCHZ	CE to output disable		30
tOHZ	OE to output disable		20



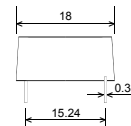
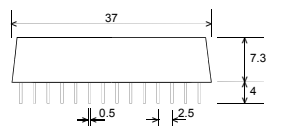
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